

IDS - 2-19-2004

PTO/SB/08A (10-01)
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U.S. Patent & Trademark Office U.S. DEPARTMENT OF COMMERCE

Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(use as many sheets as necessary)

Complete if Known

Application Number	10/721920
Filing Date	November 24, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2822
Examiner Name	Trinh, Michael

Sheet 1 of 4

Attorney Docket No: 303.685US2

US PATENT DOCUMENTS

Examiner Initial*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate

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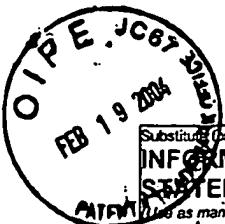
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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Sheet 2 of 4		Attorney Docket No: 303.685US2											

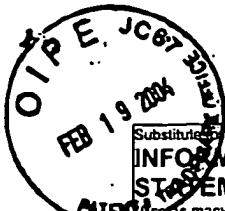
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michael Trinh

DATE CONSIDERED

2/12/04



Information Disclosure Statement by Applicant
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Approved for use through 10/31/2002, OMB 0510-0031
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Complete if Known

Application Number	10/721920
Filing Date	November 24, 2003
First Named Inventor	Ahn, Kie
Group Art Unit	2822
Examiner Name	Trinh, Michael

Sheet 4 of 4

Attorney Docket No: 303.685US2

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Michael Trinh

DATE CONSIDERED

12/12/04

Substitute Disclosure Statement Form (PTO-1449)

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹Applicant's unique citation designation number (optional) ²Applicant is to place a check mark here if English language Translation is attached

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PTO/FSB/08A(10-01)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		<i>Complete if Known</i>	
		Application Number	Unknown 10/721920
		Filing Date	Even Date Herewith
		First Named Inventor	Ahn, Kie
		Group Art Unit	Unknown 2822
		Examiner Name	Unknown
Sheet 1 of 9		Attorney Docket No: 303.685US2	

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EXAMINER *Michael Torn* DATE CONSIDERED *12/12/04*

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known				
		Application Number		Unknown 10/721,920		
		Filing Date		Even Date Herewith		
		First Named Inventor		Ahn, Kie		
		Group Art Unit		Unknown		
		Examiner Name		Unknown		
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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

		Complete if Known				
		Application Number	Unknown 10/721920			
		Filing Date	Even Date Herewith			
		First Named Inventor	Ahn, Kie			
		Group Art Unit	Unknown			
		Examiner Name	Unknown			
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		<i>Complete if Known</i>	
		Application Number	Unknown 10/721920
		Filing Date	Even Date Herewith
		First Named Inventor	Ahn, Kie
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 5 of 9		Attorney Docket No: 303.685US2	

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Substitute Disclosure Statement Form (PTO-1449)

• EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. • Applicant's unique citation designation number (optional) • Applicant is to place a check mark here if English language Translation is attached

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known				
		Application Number		Unknown 101721920		
		Filing Date		Even Date Herewith		
		First Named Inventor		Ahn, Kie		
		Group Art Unit		Unknown		
		Examiner Name		Unknown		
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		Application Number	Unknown 101721920
		Filing Date	Even Date Herewith
		First Named Inventor	Ahn, Kie
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 7 of 9		Attorney Docket No: 303.685US2	

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		Application Number	Unknown 10/721920
		Filing Date	Even Date Herewith
		First Named Inventor	Ahn, Kie
		Group Art Unit	Unknown
		Examiner Name	Unknown
Sheet 8 of 9		Attorney Docket No: 303.685US2	

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		First Named Inventor	Ahn, Kie
		Group Art Unit	Unknown
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Sheet 9 of 9		Attorney Docket No: 303.685US2	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No ¹	Include name of the author (In CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MKT		WOLF, S., "Chapter 4: Multilevel-Interconnect Technology for VLSI and ULSI", In: <u>Silicon Processing for the VLSI Era, Vol. 2 Process Integration</u> , Lattice Press, Sunset Beach, CA,(1990),176-297	

EXAMINER *michael Trib* DATE CONSIDERED *12/12/04*

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached